



FQA7N90M_F109 Information

yww.helerenter.com

For Reference Only

Part Number FQA7N90M_F109

Manufacturer Fairchild/ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 900V 7A TO-3P

Package TO-3P-3, SC-65-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









FQA7N90M_F109 Specifications

Manufacturer Part NumberFQA7N90M_F109ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-3P-3, SC-65-3SeriesQFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)900VCurrent - Continuous Drain (Id) @ 25°C7A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs52nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1880pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)210W (Tc)Rds On (Max) @ Id, Vgs1.8 Ohm @ 3.5A, 10V		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-3P-3, SC-65-3SeriesQFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)900VCurrent - Continuous Drain (Id) @ 25°C7A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs52nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1880pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)210W (Tc)Rds On (Max) @ Id, Vgs1.8 Ohm @ 3.5A, 10V	Manufacturer Part Number	FQA7N90M_F109
Package Transistors - FETs, MOSFETs - Single Package TO-3P-3, SC-65-3 Series QFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 900V Current - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 52nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1880pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 3.5A, 10V	Manufacturer	Fairchild/ON Semiconductor
Package TO-3P-3, SC-65-3 Series QFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 900V Current - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 52nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1880pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 3.5A, 10V	Category	Discrete Semiconductor Products
Series QFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 900V Current - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 52nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1880pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 3.5A, 10V		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Sv @ 250µA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 3.5A, 10V	Package	TO-3P-3, SC-65-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs MOSFET (Metal Oxide) 900V 7A (Tc) 7A (Tc) 7A (Tc) 7A (Tc) 10V 10V 10V 1250μA 5210Ψ 1880pF @ 25V 25V 25V 25V 25V 25V 25V 25V	Series	QFET?
Drain to Source Voltage (Vdss) 900V Current - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 52nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1880pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 3.5A, 10V	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 7A (Tc) 78 (Tc) 78 (Tc) 79 (Tc) 78 (Tc) 79 (T	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 52nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1880pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 3.5A, 10V	Drain to Source Voltage (Vdss)	900V
Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 52nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1880pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 3.5A, 10V	Current - Continuous Drain (Id) @ 25°C	7A (Tc)
Gate Charge (Qg) (Max) @ Vgs 52nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1880pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 3.5A, 10V	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 1880pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 3.5A, 10V	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 3.5A, 10V	Gate Charge (Qg) (Max) @ Vgs	52nC @ 10V
FET Feature - Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 3.5A, 10V	Input Capacitance (Ciss) (Max) @ Vds	1880pF @ 25V
Power Dissipation (Max) 210W (Tc) Rds On (Max) @ Id, Vgs 1.8 Ohm @ 3.5A, 10V	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs 1.8 Ohm @ 3.5A, 10V	FET Feature	-
	Power Dissipation (Max)	210W (Tc)
	Rds On (Max) @ Id, Vgs	1.8 Ohm @ 3.5A, 10V
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type Through Hole	Mounting Type	Through Hole
Supplier Device Package TO-3PN	Supplier Device Package	TO-3PN
Package / Case TO-3P-3, SC-65-3	Package / Case	TO-3P-3, SC-65-3
Report errors?		Report errors?

FQA7N90M_F109 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FQA7N90M_F109 Payment Methods





















FQA7N90M_F109 Shipping Methods













If you have any question about FQA7N90M_F109, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com